IEC 63068-1

Edition 1.0 2019-01

INTERNATIONAL STANDARD

Semiconductor devices – Non-destructive recognition criteria of defects in silicon carbide homoepitaxial wafer for power devices –
Part 1: Classification of defects

IEC Central Office
3, rue de Varembé
CH-1211 Geneva 20
Switzerland

Tel.: +41 22 919 02 11
info@iec.ch
www.iec.ch

About the IEC
The International Electrotechnical Commission (IEC) is the leading global organization that prepares and publishes International Standards for all electrical, electronic and related technologies.

About IEC publications
The technical content of IEC publications is kept under constant review by the IEC. Please make sure that you have the latest edition, a corrigendum or an amendment might have been published.

IEC publications search - webstore.iec.ch/advsearchform
The advanced search enables to find IEC publications by a variety of criteria (reference number, text, technical committee,…). It also gives information on projects, replaced and withdrawn publications.

IEC Just Published - webstore.iec.ch/justpublished
Stay up to date on all new IEC publications. Just Published details all new publications released. Available online and once a month by email.

IEC Customer Service Centre - webstore.iec.ch/csc
If you wish to give us your feedback on this publication or need further assistance, please contact the Customer Service Centre: sales@iec.ch.

Electropedia - www.electropedia.org
The world's leading online dictionary on electrotechnology, containing more than 22 000 terminological entries in English and French, with equivalent terms in 16 additional languages. Also known as the International Electrotechnical Vocabulary (IEV) online.

IEC Glossary - std.iec.ch/glossary
67 000 electrotechnical terminology entries in English and French extracted from the Terms and Definitions clause of IEC publications issued since 2002. Some entries have been collected from earlier publications of IEC TC 37, 77, 86 and CISPR.

IEC 63068-1

Edition 1.0 2019-01

INTERNATIONAL STANDARD

Semiconductor devices – Non-destructive recognition criteria of defects in silicon carbide homoepitaxial wafer for power devices – Part 1: Classification of defects

INTERNATIONAL ELECTROTECHNICAL COMMISSION

ICS 31.080.99

ISBN 978-2-8322-6479-9

CONTENTS

INTERNATIONAL ELECTROTECHNICAL COMMISSION

_____

SEMICONDUCTOR DEVICES – NON-DESTRUCTIVE RECOGNITION CRITERIA OF DEFECTS IN SILICON CARBIDE HOMOEPITAXIAL WAFER FOR POWER DEVICES –

Part 1: Classification of defects

FOREWORD

1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
2) The formal decisions or agreements of IEC on technical matters express, as nearly as possible, an international consensus of opinion on the relevant subjects since each technical committee has representation from all interested IEC National Committees.
3) IEC Publications have the form of recommendations for international use and are accepted by IEC National Committees in that sense. While all reasonable efforts are made to ensure that the technical content of IEC Publications is accurate, IEC cannot be held responsible for the way in which they are used or for any misinterpretation by any end user.
4) In order to promote international uniformity, IEC National Committees undertake to apply IEC Publications transparently to the maximum extent possible in their national and regional publications. Any divergence between any IEC Publication and the corresponding national or regional publication shall be clearly indicated in the latter.
5) IEC itself does not provide any attestation of conformity. Independent certification bodies provide conformity assessment services and, in some areas, access to IEC marks of conformity. IEC is not responsible for any services carried out by independent certification bodies.
6) All users should ensure that they have the latest edition of this publication.
7) No liability shall attach to IEC or its directors, employees, servants or agents including individual experts and members of its technical committees and IEC National Committees for any personal injury, property damage or other damage of any nature whatsoever, whether direct or indirect, or for costs (including legal fees) and expenses arising out of the publication, use of, or reliance upon, this IEC Publication or any other IEC Publications.
8) Attention is drawn to the Normative references cited in this publication. Use of the referenced publications is indispensable for the correct application of this publication.
9) Attention is drawn to the possibility that some of the elements of this IEC Publication may be the subject of patent rights. IEC shall not be held responsible for identifying any or all such patent rights.

International Standard IEC 63068-1 has been prepared by IEC technical committee 47: Semiconductor devices.

The text of this International Standard is based on the following documents:

CDV	Report on voting
47/2474/CDV	47/2521A/RVC

Full information on the voting for the approval of this International Standard can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 63068 series, published under the general title *Semiconductor devices – Non-destructive recognition criteria of defects in silicon carbide homoepitaxial wafer for power devices*, can be found on the IEC website.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "http://webstore.iec.ch" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

INTRODUCTION

Silicon carbide (SiC) is widely used as a semiconductor material for next-generation power semiconductor devices. SiC, as compared with silicon (Si), has superior physical properties such as a higher breakdown electric field, higher thermal conductivity, lower thermal generation rate, higher saturated electron drift velocity, and lower intrinsic carrier concentration. Their attributes realize SiC-based power semiconductor devices with faster switching speeds, lower losses, higher blocking voltages, and higher temperature operation relative to standard Si-based power semiconductor devices.

SiC-based power semiconductor devices are not fully realized due to high costs, low yield, and perceived reliability concerns. One of the serious issues lies in the defects existing in SiC homoepitaxial wafers. Although an effort of decreasing defects in the SiC homoepitaxial layer is actively implemented, there are a number of defects (approximately 1 000 defects/cm^2) in commercially available SiC homoepitaxial wafers. Therefore, it is indispensable to establish an international standard regarding the quality assessment of SiC homoepitaxial wafers.

The IEC 63068 series of standards is planned to comprise Part 1, Part 2, and Part 3, as detailed below. The outline of this Part 1 is to list, illustrate and provide reference for various characteristic features and defects that are observed on SiC homoepitaxial wafers of crystallographic polytype 4H used in high-power semiconductor device manufacturing.

Part 1: Classification of defects

Part 2: Test method for defects using optical inspection

Part 3: Test method for defects using photoluminescence

SEMICONDUCTOR DEVICES – NON-DESTRUCTIVE RECOGNITION CRITERIA OF DEFECTS IN SILICON CARBIDE HOMOEPITAXIAL WAFER FOR POWER DEVICES –

Part 1: Classification of defects

1 Scope

This part of IEC 63068 gives a classification of defects in as-grown 4H-SiC (Silicon Carbide) epitaxial layers. The defects are classified on the basis of their crystallographic structures and recognized by non-destructive detection methods including bright-field OM (optical microscopy), PL (photoluminescence), and XRT (X-ray topography) images.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

There are no normative references in this document.

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at http://www.electropedia.org/
- ISO Online browsing platform: available at http://www.iso.org/obp

3.1
silicon carbide
SiC
semiconductor crystal composed of silicon and carbon, which exhibits a large number of polytypes such as 3C, 4H, and 6H

Note 1 to entry: A symbol like 4H gives the number of periodic stacking layers (2, 3, 4,…) and the crystal symmetry (H = hexagonal, C = cubic) of each polytype.

3.2
3C-SiC
SiC crystal with zinc blende structure, in which three Si-C layers are periodically arranged along the <111> direction

3.3
4H-SiC
SiC crystal showing a hexagonal symmetry, in which four Si-C layers are periodically arranged along the crystallographic c-axis

Note 1 to entry: The crystal structure of 4H-SiC is similar to wurtzite with a unit cell having four periodical occupied sites along the <0001> direction.